



4W NVZ I ZL VTI CMI VL TM S CMK ZW

4W QL KI VKM X KS CM

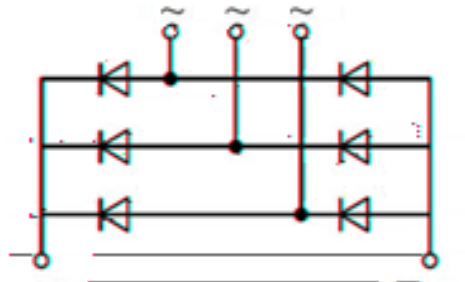
0QP ZMK ZW K X JQ

:: 5		
1		)
1 5 (8 U		)
. 5I		

. QIL XXb NVZ, + U VWZ

4QM ZK QVZ NVZ Z V Q WZM) + U VWZ KW ZVWZ

6 VW KW ZVW JTM ZK QVZ NVZ) + , + KW MZMZ



(+ + VTI WPMZ QM XKQDL

: MMQMXM SZM MZM VTI CM		:: 5		
6 VW ZMMQMXM SZM MZM VTI CM		: 5		
7 X K ZW	+ °C	1		)
. VZ I ZL ZMK ZW	KaKM QM I M 0b R °C	1 5		)
1 I TMNVN QO		1		)
: 5 QVT QW VTI CM	) + 0b UQ	1 7		
2 VK QW MU XWZ ZMZ VCM		2	f	
VZ CM MU XWZ ZMZ VCM		o	f	°C



(+ + VM WPMZ QM XKQDL

. VZ I Z VII OM	1) R °C	.			
: MMZMTM S QMK ZW	: ::5 R °C	1:5			U)
	: ::5 R °C				U)
PZM PWL VII OM	. VZXW MZTW K K T QWVW	7			
, aM U Q M QI VM	R °C	Z			U

(+ + VM WPMZ QM XKQDL

PMZUI TO XLI VM R VK W WK M	XVZLQVM	: PRK			3
5 WVQO WY M	I MXT M WPM QS KZM 5	5			6 U
	- TK ZVM WMUQI T KZM 5				6 U

25, , ,	25, , ,	,	O8+	8+	8+

FIG.1: Forward characteristics(per diode)

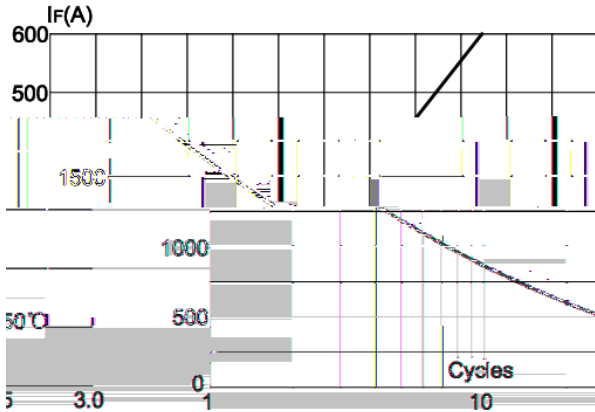
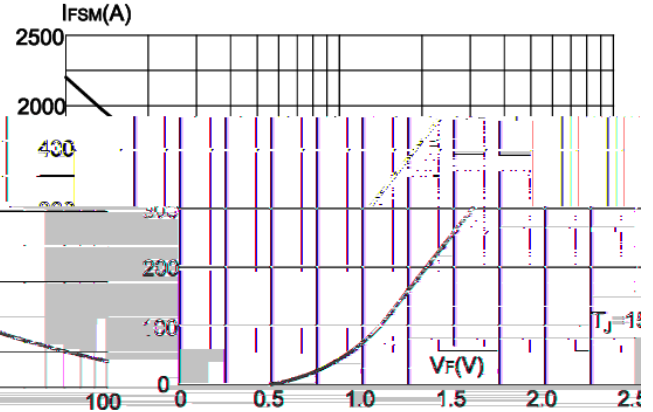


FIG.2: Peak on-state surge current



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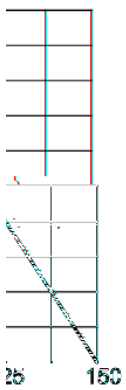


FIG.4: Maximum transient thermal impedance
 $R_{th(j-c)}$ (°C/W) Junction-to-case(per diode)

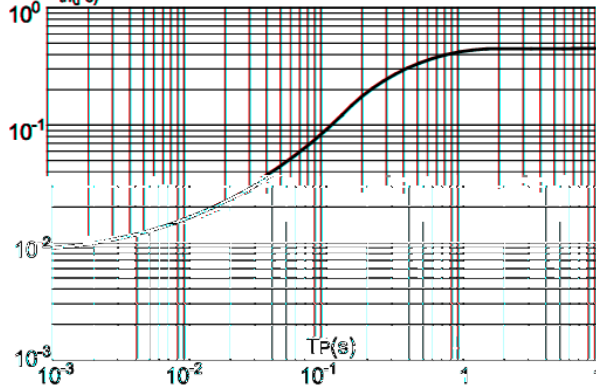
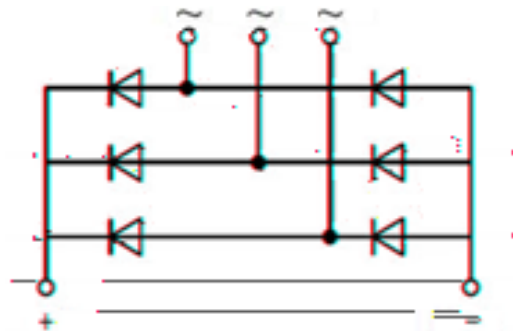
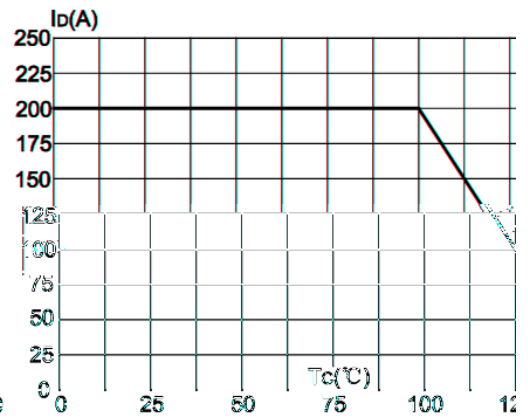


FIG.3: Forward current vs. case temp







1MVZUI QW N Z/QPML Q PQ LVK UMW Q JMTD ML WJMIKK Z MI VL ZMTJTM OW MMZ
2QVO 20201 MUQWL KVZ+W 4LI UM WZM XW QQa NVZ PMKW MY MKM VN M
PW KW QMZ QWNZ KPQNZUI QW WZ MJM VWL Q PQ QNZUI QW Q PQLVK UMW
Q JMK WKPI VOM QW XQZ WGM 6W Q I VL QO PQ 2QVO 20201 QN Tã KW Xã
Q PM MZ W TML QI QML IOZMUM 8Z/L K I VL QNZUI QW XZVQML Q PQ
LVK UMW PI MWWOQZUM VIX M 2QVO 20201 UM WZM XW QQa NVZ Va
QZQUM VWPVZOP VWPZ XZQ PPUia ZM TNW PM MVN KP XZ/L K I VL
QNZUI QW PQ LVK UMW Q PM QQT ZM M LI ML 2ã PQ LVK UMW
XVZMLM I VL ZXTKM I TQNZUI QW XZM Qã XTDL

 Q ZQQML ZLMUI ZV2QVO 20201 MUQWL KVZ+W 4 2QVO 20201
MUQWL KVZ+W 4L) TZOP ZMMZML